



SPP1073

P-Channel Enhancement Mode MOSFET

DESCRIPTION

The SPP1073 is the P-Channel enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology. This high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and other battery powered circuits where high-side switching , low in-line power loss, and resistance to transients are needed.

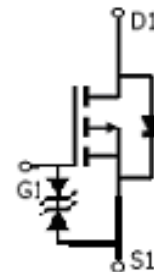
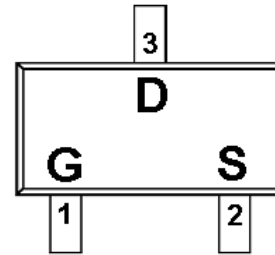
FEATURES

- ◆ P-Channel
 -30V/0.45A, $R_{DS(ON)} = 0.65\Omega @ V_{GS} = -4.5V$
 -30V/0.35A, $R_{DS(ON)} = 0.90\Omega @ V_{GS} = -2.5V$
 -30V/0.25A, $R_{DS(ON)} = 1.5\Omega @ V_{GS} = -1.8V$
- ◆ Super high density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOT-723 package design

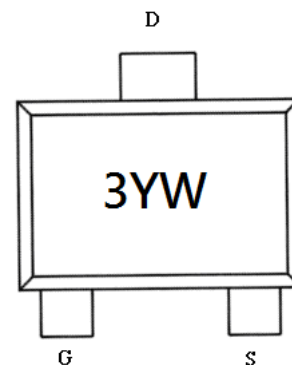
APPLICATIONS

- Drivers : Relays/Solenoids/Lamps/Hammers
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

PIN CONFIGURATION(SOT-723)



PART MARKING





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PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

ORDERING INFORMATION

Part Number	Package	Part Marking
SPP1073S72RGB	SOT-723	3

※ SPP1073S72RGB : Tape Reel ; Pb – Free, Halogen – Free

ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit	
Drain-Source Voltage	V _{DSS}	-30	V	
Gate –Source Voltage	V _{GSS}	±12	V	
Continuous Drain Current(T _J =150°C)	I _D	TA=25°C	-0.45	A
		TA=80°C	-0.35	
Pulsed Drain Current	I _{DM}	-1.0	A	
Continuous Source Current(Diode Conduction)	I _S	-0.3	A	
Power Dissipation	P _D	TA=25°C	0.27	W
		TA=70°C	0.16	
Operating Junction Temperature	T _J	-55/150	°C	
Storage Temperature Range	T _{STG}	-55/150	°C	



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ELECTRICAL CHARACTERISTICS

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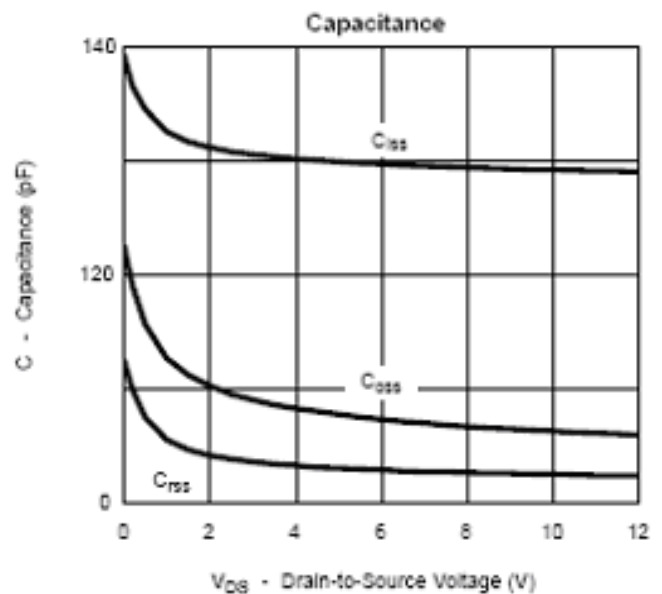
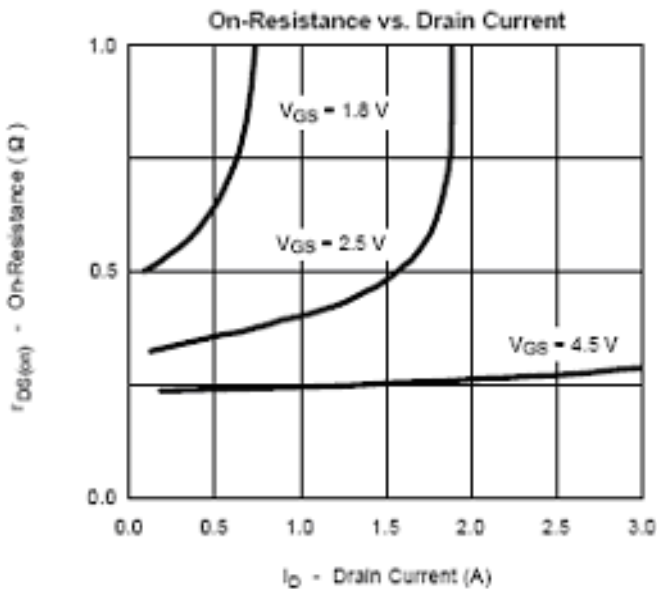
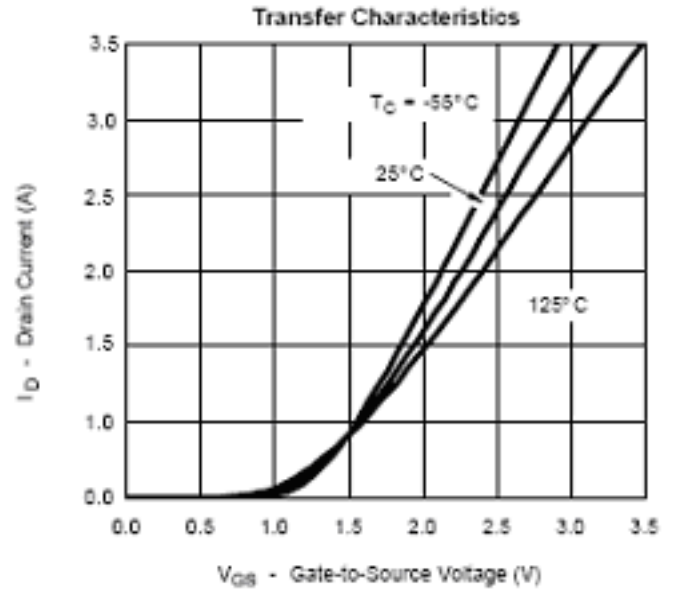
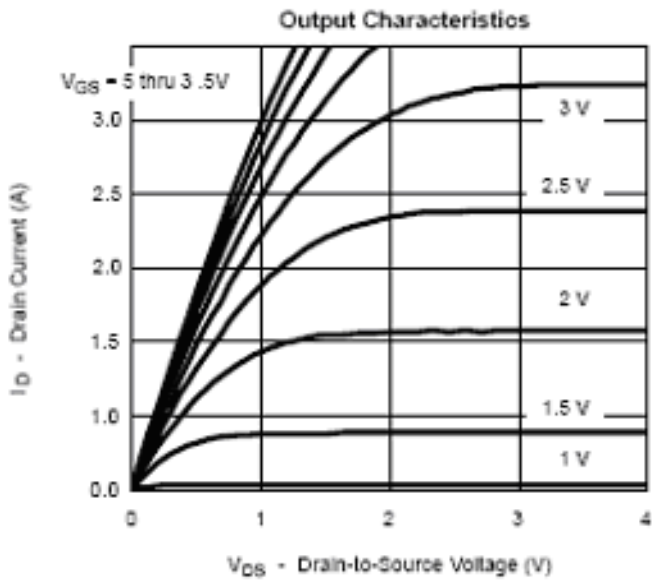
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.35		-1.0	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 12V$			± 30	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-24V, V_{GS}=0V$			-1	μA
		$V_{DS}=-24V, V_{GS}=0V$ $T_J=55^\circ C$			-5	
On-State Drain Current	$I_{D(on)}$	$V_{DS}\leq -4.5V, V_{GS}=-5V$	-0.7			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-0.45A$			0.65	Ω
		$V_{GS}=-2.5V, I_D=-0.35A$			0.90	
		$V_{GS}=-1.8V, I_D=-0.25A$			1.50	
Forward Transconductance	g_{fs}	$V_{DS}=-10V, I_D=-0.25A$		0.4		S
Diode Forward Voltage	V_{SD}	$I_S=-0.15A, V_{GS}=0V$		-0.8	-1.2	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=-10V, V_{GS}=-4.5V, I_D=-0.6A$		1.5	2.0	nC
Gate-Source Charge	Q_{gs}			0.3		
Gate-Drain Charge	Q_{gd}			0.35		
Turn-On Time	$t_{d(on)}$	$V_{DD}=-10V, R_L=10\Omega, I_D=-0.4A$ $V_{GEN}=-4.5V, R_G=6\Omega$		5	10	ns
	t_r			15	25	
Turn-Off Time	$t_{d(off)}$			8	15	
	t_f			1.4	1.8	



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TYPICAL CHARACTERISTICS

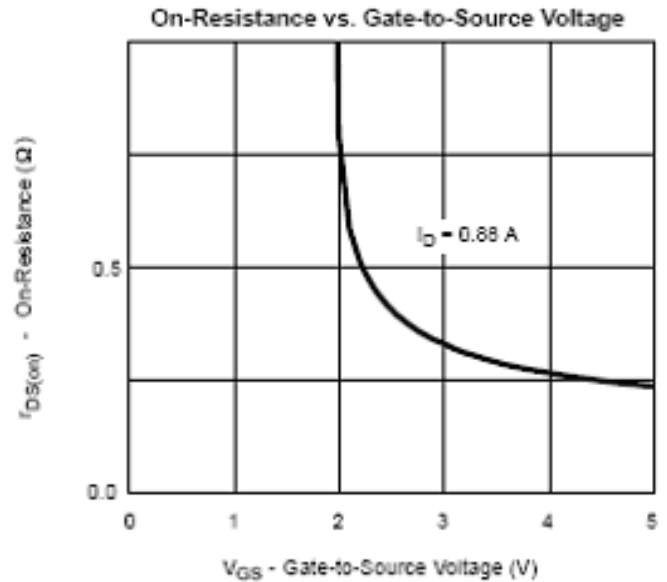
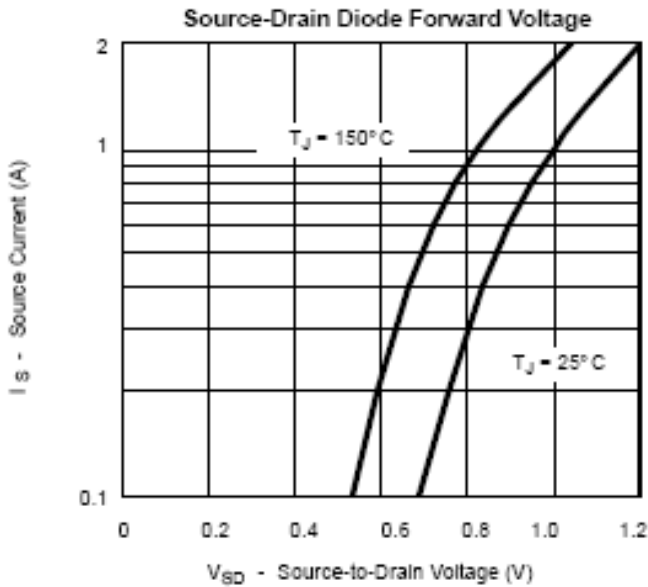
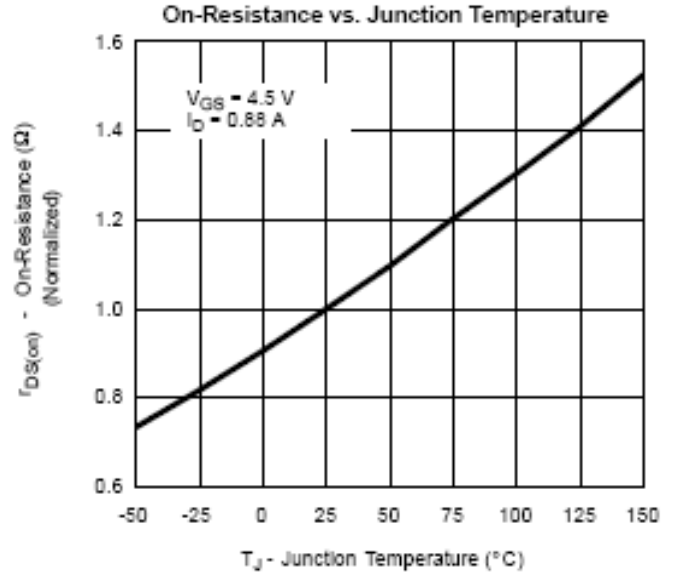
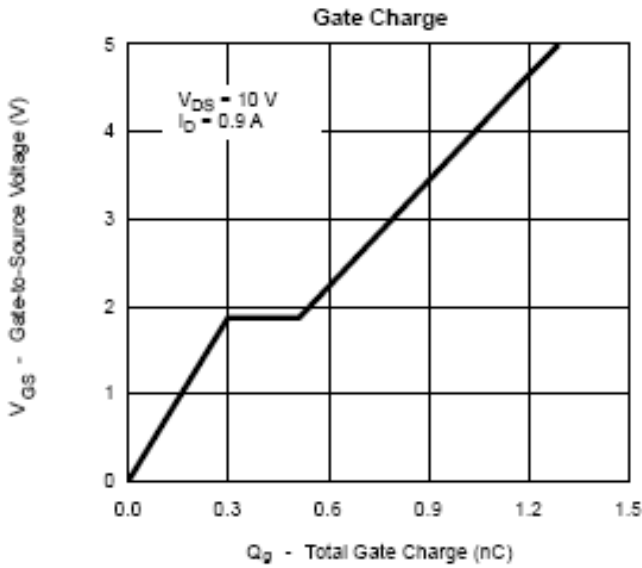




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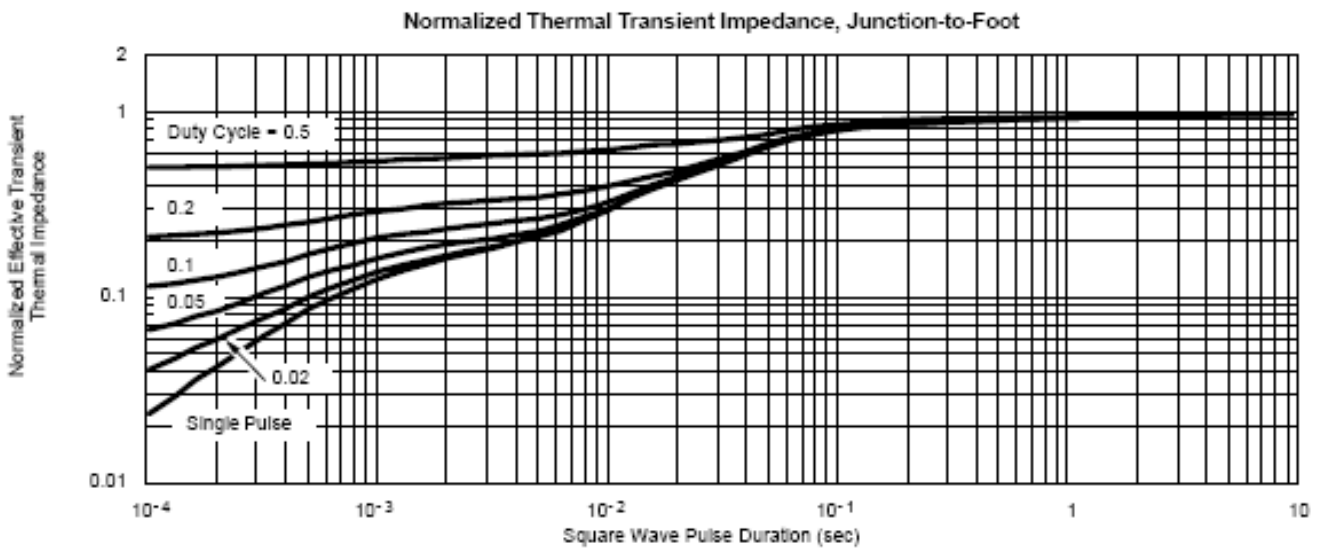
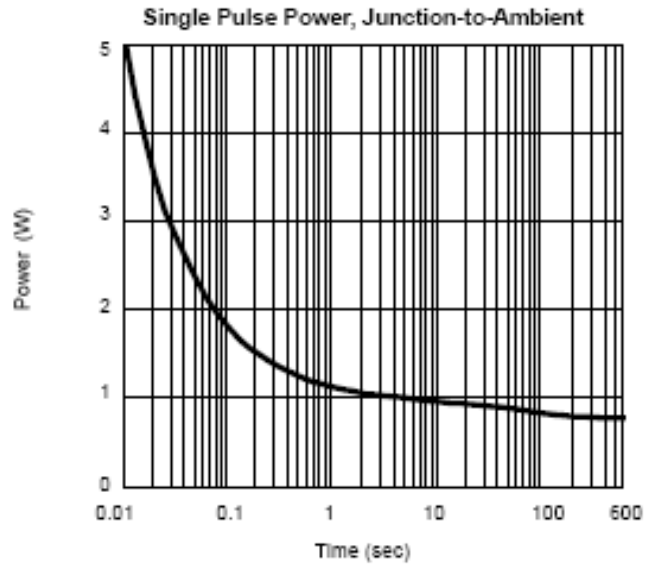
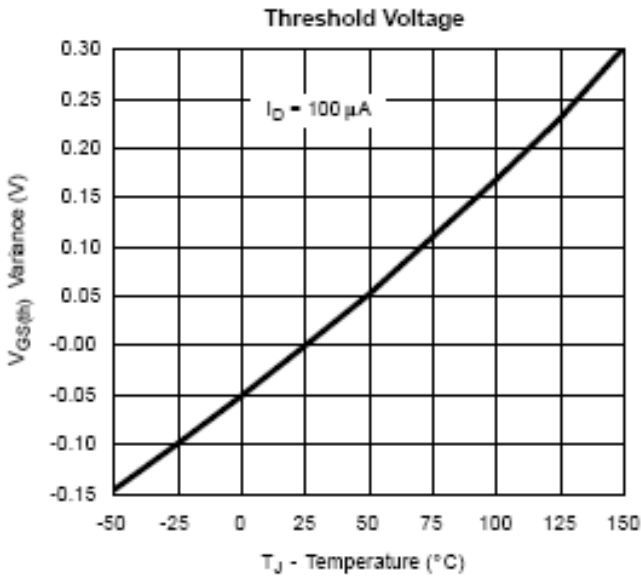




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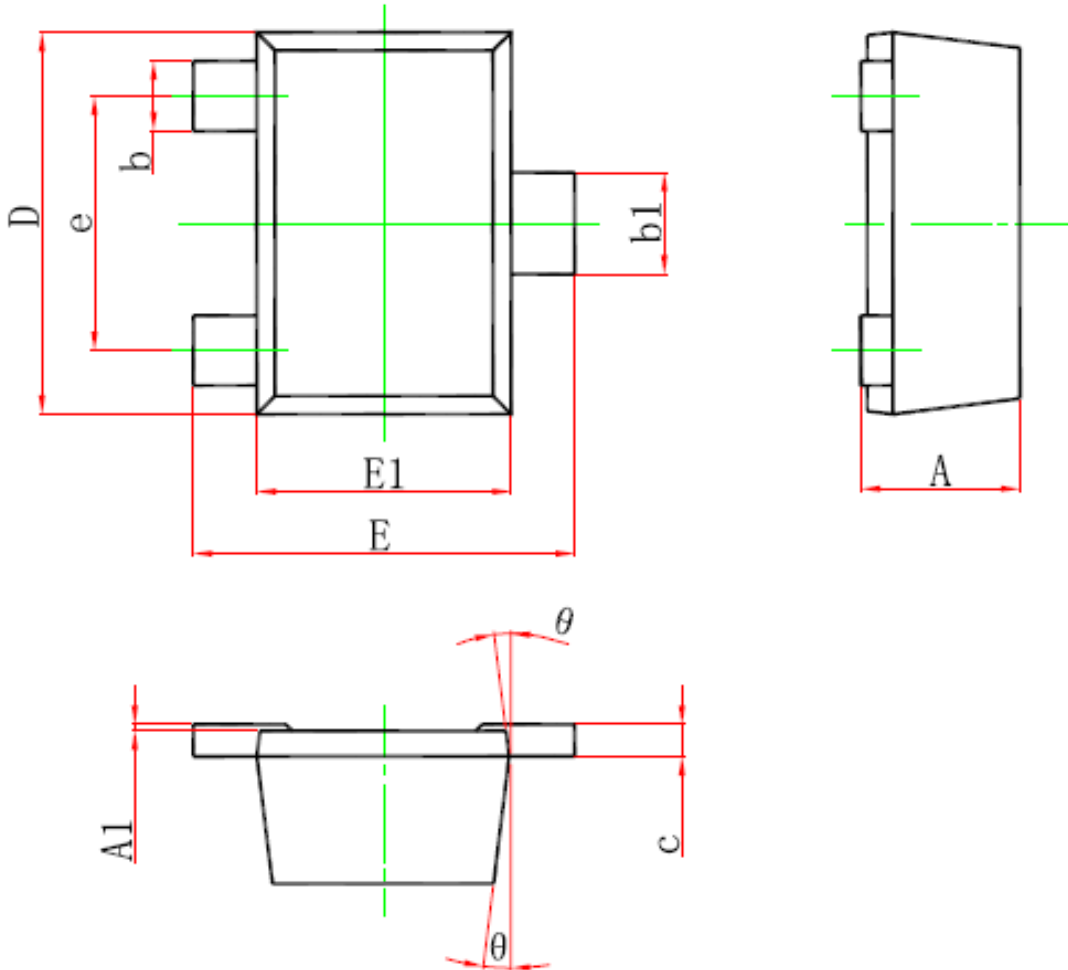




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SOT-723 PACKAGE OUTLINE



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A		0.500		0.020
A1	0.000	0.050	0.000	0.002
b	0.170	0.270	0.007	0.011
b1	0.270	0.370	0.011	0.015
c		0.150		0.006
D	1.150	1.250	0.045	0.049
E	1.150	1.250	0.045	0.049
E1	0.750	0.850	0.030	0.033
e	0.800 TYP.		0.031 TYP.	
θ	7° REF.		7° REF.	



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